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Bachelor Thesis in Physics submitted by

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Calibration of BrainScaleS PowerIt Subsystem and Regulating a BrainScaleS Power Supply

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Abstract

The Powerlts main purpose is to measure and supply different voltages. In the Human Brain Projects BrainScaleS system, it delivers power to all system components. This thesis will provide a calibration of the Powerlt board as well as a regulation mechanism for its 1.8V power supplies.

Calibration of this board, will provide more accurate measurements, and allow for later regulation of its 1.8V outputs. First its circuitry will be examined and their behavior tested, from which these circuits can be calibrated. With these calibrations a method for regulating both of its 1.8V power supplies will be implemented.

This thesis also contains the changes done to the Powerlt firmware while working on these tasks. The new firmware now has a new protocol for communication over a l^2C . It can be used for accessing any calibration parameter or on board measurement.

Zusammenfassung

Die Hauptaufgabe des Powerlts ist die Messung von und Versorgung mit verschiedenen Spannungen. Es versorgt alle Komponenten im BrainScaleS System des Humen Brain Projekts.

Diese Arbeit liefert eine Kalibration des Powerlt, sowie eine Methode zur Regelung der 1.8 V Spannungsausgänge eines Powerlt. Zuerst werden dafür die verbauten Schaltungen untersucht und auf ihr verhalten getestet und daraus können Kalibrationsdaten erfasst werden. Die spätere Regulierung der 1.8 V Ausgänge hängt dabei von der vorausgegangenen Kalibrierung ab.

Zusätzlich enthällt diese Arbeit die Änderungen, die an der Firmware vorgenommen worden sind, während diese Aufgaben bearbeitet wurden. Die neue Firmware enthällt nun ein neues protocol für die Kommunikation über einen I²C-Bus. Dieses Protokoll kann dazu genutzt werden auf beliebige Kalibrationsdaten oder Messwerde zuzugreifen.

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1 Introduction

This will be a short introduction to the BrainScaleS System and Powerlt.

1.1. The BrainScaleS System

The BrainScaleS Wafer System which is visualized in figure 1.1, developed and used in the electronic visions group at Heidelberg University is a neuromorphic hardware implementation [1]. On this Hardware, mixed-signal ASICs, or also called HICANNs, implement a behavior similar to that of a neuron found in biological systems. These ASIC chips are placed on a silicon wafer, and grouped into packs of 8, called reticles. With these Chips complex behavior of biological systems can be simulated.

Focus of this thesis is part of the hardware implementation and only the following components will either be further examined or used later on:

• Control Units for Reticles, short CURe boards

These boards control the power delivery mechanism for each of the 48 reticles.

• Analog Breakout boards, AnaB for short

Provided by these boards are direct connections to reticle voltages, two per reticle. These are normally shared between all 8 reticles.

• and power supply, called PowerIt.

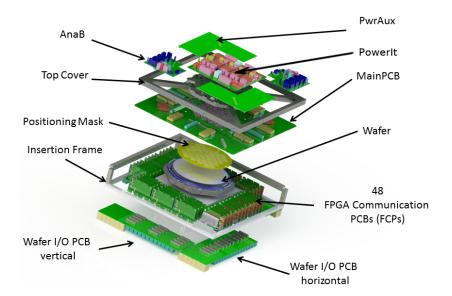


Figure 1.1.: The BrainScaleS wafer-scale hardware system, marked are the main components comprising a single wafer system. [2]

1.2. About the Powerlt Subsystem

The main subject of this thesis is the Powerlt board, photographed in figure 1.2. It functions as power supply inside of the WaferScale system, described before, in which it provides e.g. the wafer with 1.8 V and the FPGAs with 9.6 V. Its maximum rated power draw is 2 kW. [3] This Powerlt board has a integrated STM32 microcontroller¹ which runs a custom firmware based

on ChibiOS [5]. The Powerlt also measures the following values:

- input voltage and current
- 1.8 V output voltage and current each for analog and digital parts of the wafer circuits
- and the 9.6 V output voltage

which can then be used inside the firmware.

The input voltage, nominal, is 48 V and therefore the input current should not exceed 41.7 A dditionally the 9.6 V are a set voltage obtained by the power supply modules², which divide the input voltage by 5. Lastly the 1.8 V output voltage is variable.

¹STM32F405RGT [4]

²5:1 Bus converter IB0xxE096T48xx, 500W each

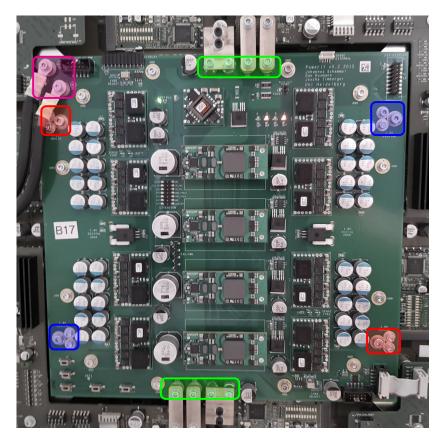


Figure 1.2.: Photograph of the Powerlt boards top view. It receives 48 V as input (magenta) and provides 9.6 V (green) and 1.8 V (analog: red, digital: blue)

1.3. Contents in Detail

The first goal was to be able to change the calibration parameters. An upgrade for the Powerlt firmware was added to accomodate for those values. This was accomplished with a virtual memory map, which maps every parameter to a specific location and all of them can be changed.

Calibrating the Powerlt was the next task. The calibration characterizes the voltage measuring circuits, whose voltages are either coming into or leaving the Powerlt. Additionally there are a current measuring circuits for incoming current and both 1.8 V output currents. A reference voltage measurement was used to generate a fitted polynomial. This polynomials coefficients are the calibration parameters used inside the Powerlt.

Taking these calibrations as basis, the 1.8 V power supplies' behavior through different current draws could be observed. A simple model was generated from these measurements and applied. Also inside the formware a first iteration of that model was implemented and could now be tested.

This all resulted in the testing and quntification of the regulation mechanism, as well as a secondary model that could be used in the future.

2 Theory

This chapter will be discussing the principles used in the experiments. These will contain simplified circuits and their respective equations as well as component behavior as specified in their respective data sheets by their manufacturer

2.1. Hardware Component Behavior

Before discussing the experimental results it needs to be clear what circuitry is used in these experiments and what behavior we expect. Keeping in mind, that these are theoretical values and will most likely not be exactly the same as those found in actual hardware, as all values given will always be within some error.

Each of the three voltage regimes that will be observed on the Powerlt board, 48V, 9.6V and 1.8V, has a voltage- and in the cases of 48V and 1.8V also a current-measurement circuit. Additionally there is a temperature sensor built into the STM32 chip.

2.1.1. ADC Calibration

The measurements will be done by the STM32-Chip, which uses 12bit ADCs. A single ADC will be switching between all connected pins. This Behavior can be problematic in regards to measuring accurately. The timing used to measure a single pin can be programmatically set from 3 up to 480 clock ticks¹

2.1.2. 48V Input Voltage

The circuits for measuring input voltage and current are the most complex. For voltage measurement the circuit needs to

- divide our input voltage into a usable potential range
- decouple the input (48 V) from signal potential (3.3 V)
- and amplify the voltage, to be in the STM32-Chips Voltage range of up to 3.3 V.

The already implemented circuit can be seen in figure 2.1.

It consists of a 1:240 voltage divider, a full differential isolation amplifier taking in the roughly 200 mV (nominal voltage range), and amplifying it by a factor of 8 ($r_{diffOpAmp}$ [6]). It is also decoupling the input and output voltages, so our 48V and 3.3V circuit parts are electrically

 $^{^{1}\}mathrm{this}\ \mathrm{clock}$ is the internal adc clock, with a frequency of 159 Hz

insulated. The remaining operational amplifier provides difference to single ended conversion with an amplification or 1.1 (r_{OpAmp})

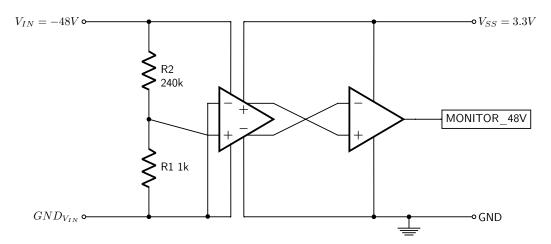


Figure 2.1.: Circuit for measuring the 48 V input voltage, consisting of input potential (left), two resistors as voltage divider, one fully differential isolation amplifier (left), one operational Amplifier (right), output voltage as well as the connection to the STM32-Chips input pin (right)

This circuit results in the following equation for calculating the input voltage from a pin voltage:

$$V_{48V \text{ in}} \cdot \frac{R_1}{R_1 + R_2} \cdot r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}} = V_{\text{MONITOR}_48V}$$

$$\Leftrightarrow \frac{V_{\text{MONITOR}_48V}}{r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}}} \cdot \frac{R_1 + R_2}{R_1} = V_{48V \text{ in}} \qquad (2.1)$$

and the extremes, when assuming $(48.0\pm4.8)\,V$ are

$$V_{\text{MONITOR}_{48V, \min}} = 43.2 \,\text{V} \cdot \frac{1}{240+1} \cdot 8 \cdot 1.1 = 1.5774 \,\text{V}$$
 (2.2)

$$V_{\text{MONITOR}_{48V, \text{max}}} = 52.8 \,\text{V} \cdot \frac{1}{240+1} \cdot 8 \cdot 1.1 = 1.9280 \,\text{V}$$
 (2.3)

The ADCs 12bit gives a maximum resolution of 2.1 mV.

2.1.3. 48 V Input Current

The circuit has to satisfy the following constraints:

- use a shunt resistor, with minimal heat dissipation
- while still providing a good resolution within the STM32-Chips specifications

To accomplish that, the circuit is measuring the voltage over a $500 \,\mu\Omega$ shunt Resistor, while a current is flowing. By Ohms Law that results in a linear proportionality between current an the

obtained voltage. Which is then decoupled and amplified by a factor of 8, as well as converted from a difference to single ended voltage, with a amplification factor of 1.1.

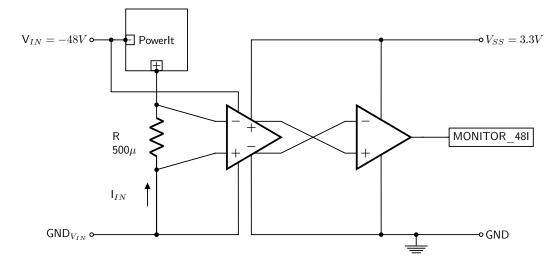


Figure 2.2.: Circuit for measuring the 48 V input current, consisting of Powerlt, one shunt-resistor, one full diff isolating Amplifier, one operational amplifier, output potential, as well as the connection to the STM32-Chips input pin

Here the same amplifiers as in subsection 2.1.2 is used and so we can apply the following equation for our input current:

$$I_{48V \text{ IN}} \cdot R_{\text{shunt}} \cdot r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}} = V_{481 \text{ pin}}$$

$$\Leftrightarrow \quad \frac{V_{481 \text{ pin}}}{R_{\text{shunt}}} \cdot \frac{1}{r_{\text{diffOpAmp}} \cdot r_{\text{OpAmp}}} = I_{48V \text{ IN}}$$
(2.4)

The current range is from 0 A up to 41.7 A (= 2 kW / 48 V)and gives a resulting observable voltage range from 0 V to:

41.7 A
$$\cdot$$
 500 $\mu\Omega \cdot 8 \cdot 1.1 = 0.1833$ V (2.5)

This results in a maximum resolution of 0.18 A.

2.1.4. 9.6V Output Voltage

The measurement of 9.6 V is quite simpler. This Circuit consists of a 1:3 Voltage Divider.

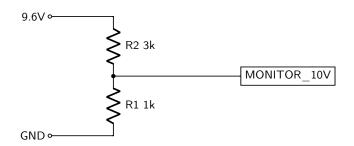


Figure 2.3.: Circuit for measuring 9.6V output voltage. Consisting of a voltage divider with 1:4 ratio, input voltage (left) and output voltage (right)

To describe that circuit the following equation can be used:

$$\frac{V_{9.6V \text{ IN}} \cdot R_1}{R_1 + R_2} = V_{\text{MONITOR}_10V}$$
(2.6)

$$\Leftrightarrow \frac{V_{\text{MONITOR}_10V}}{R_1} \cdot (R_1 + R_2) = V_{9.6V \text{ IN}}$$
(2.7)

2.1.5. 1.8V Output Voltage

This Voltage is measured directly with the STM32-Chip.

Until now the voltages and currents could only be measured, now the mechanism for setting a resulting voltage at the 1.8 V terminals is known. The circuit for generating 1.8 V can be seen in figure 2.4. It consists of a power module and the three resistors R_{series} , $R_{parallel}$ and R_{pot} . The resistances set the output to a given voltage of around 1.8 V. Based on R_{pot} this voltage is varied, because resistance is settable via a digital potentiometer².

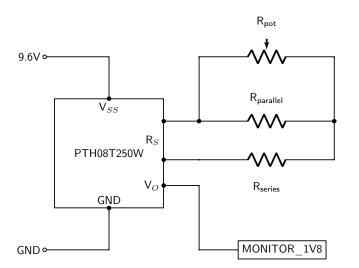


Figure 2.4.: Schema of a 1.8V supply circuit. It features a DC-DC Converter, a resistor chain, supply voltage (left) and resulting voltage (V_O).

The in figure 2.4 used 1.8 V converter has a characteristic output voltage formula [8], written in equation 2.10. The in this circuit used $10 \text{ k}\Omega$ potentiometer is linear.

²MCP4152 digital potentiometer [7]

Therefore equations 2.8, 2.9 and 2.10 describe the circuit.

$$R_{\text{pot}} = P_{\text{val}} \frac{10 \,\text{k}\Omega}{256} \tag{2.8}$$

$$R_{S} = \left(\frac{1}{R_{\text{pot}}} + \frac{1}{R_{\text{parallel}}}\right)^{-1} + R_{\text{series}}$$
$$= \frac{R_{\text{pot}} \cdot R_{\text{parallel}}}{R_{\text{pot}} + R_{\text{parallel}}} + R_{\text{series}}$$
(2.9)

$$V_{\text{MONITOR}_1V8} = \frac{30.1 \,\text{k}\Omega}{R_S + 6.49 \,\text{k}\Omega} \cdot 0.7 \,\text{V} + 0.7 \,\text{V}$$
(2.10)

Visualizing the equation 2.9 results in figure 2.5, in which the limits of this circuit are visible.

$$V_{\text{MONITOR 1V8, min}} = 1.549 \, \text{V}$$
 (2.11)

$$V_{\text{MONITOR 1V8, max}} = 2.022 \,\text{V}$$
 (2.12)

And these extremes will be a limiting factor later on. Also with 12bit ADCS that results in a maximum resolution of 0.8 mV.

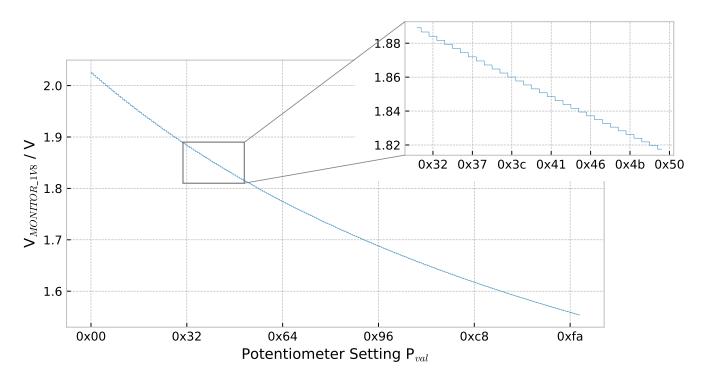


Figure 2.5.: Expected behavior curve of 1.8V output voltage vs potentiometer setting. Shown is the complete range of possible settings and their resulting voltage. The zoomed in partial view shows, that because the setting can only be of integer value any resulting values are also discrete. A single step can increase the voltage by somewhere between 1.0545 mV and 3.2500 mV

2.1.6. 1.8V Output Current

The outgoing current over 1.8V is measured by a hall sensor, which outputs a voltage to be measured. Each connection (digital and analog) has this sensor in series to its load.

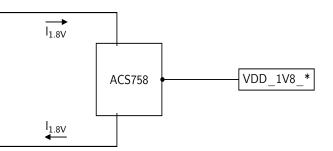


Figure 2.6.: Circuit for measuring 1.8V current. It features a ACS758 hall sensor, input voltage (left) and output voltage (right)

The hall sensor is rated for a maximum constant current draw of 100A, and features the following behavior:

$$I_{1.8V, in} \cdot 0.004 \, V \, A^{-1} + 0.12 \, V = V_{\text{MONITOR 118}} \tag{2.13}$$

By applying the limits of 0 A and 100 A, the following voltage range can be observed:

$$0 \mathsf{A} \cdot 0.004 \mathsf{V} \mathsf{A}^{-1} + 0.12 \mathsf{V} = 0.12 \mathsf{V}$$
(2.14)

$$100 \,\mathsf{A} \cdot 0.004 \,\mathsf{V} \,\mathsf{A}^{-1} + 0.12 \,\mathsf{V} = 0.52 \,\mathsf{V} \tag{2.15}$$

These values and the used 12bit ADCs gives a maximum resolution of around 0.2 A

2.2. 1.8V Output Regulation

The method for regulating the 1.8 V output voltage consists of two parts.

First the voltage, wanted at the output terminal and second the corresponding potentiometer setting to use for that voltage On the other hand, to calculate the voltage to output, it is necessary to classify the connections between the Powerlts output terminals and reticles.

2.2.1. Potentiometer Mapping

Combining Equations 2.8, 2.9, and 2.10, we gather equation 2.16. This equation maps a given output voltage to a corresponding potentiometer setting (reverse to figure 2.5).

$$P_{\text{val}} = \frac{R_{\text{par}} \left[\left(\frac{0.7V \cdot 30.1k\Omega}{V_O - 0.7V} - 6.49k\Omega \right) - R_{\text{ser}} \right]}{R_{\text{par}} + \left(\frac{0.7V \cdot 30.1k\Omega}{V_O - 0.7V} - 6.49k\Omega \right) - R_{\text{ser}}} \cdot \frac{256}{10k\Omega}$$
(2.16)

This mapping will be converted into a lookup table before the PowerIt firmware is initiated.

2.2.2. Power Wafer

To test the 1.8V regulation the so called PowerWafer is going to be used. Its reticles can be controlled via the CURE board, similar to HICANN wafers, which are used in BrainScaleS. But the Power Wafer is different, as it cannot be used for any neuromorphic computation. Its internals are ohmic resistors, which provide a maximum power draw per reticle of what is possible inside a usable wafer module.

It has the same layout as its system counterparts and each of the 48 reticles can be accessed, digitally as well as electrically.

And like its system counterparts it is placed on a MainPCB (see figure 2.7). All CURE boards connect to it and control the PowerFETs, as well as provide voltage readout from each reticle. The CURE boards read right before R_1 in figure 2.8.

Also on the MainPCB are the AnaB boards. Note that here lies another specialization of the PowerWafer. All reticles' analog and digital 1.8 V lines are connected directly to pins on the analog readout boards [9]. There it is possible to access a voltage, which is measured after the load resistors in figure 2.8 (after [1])

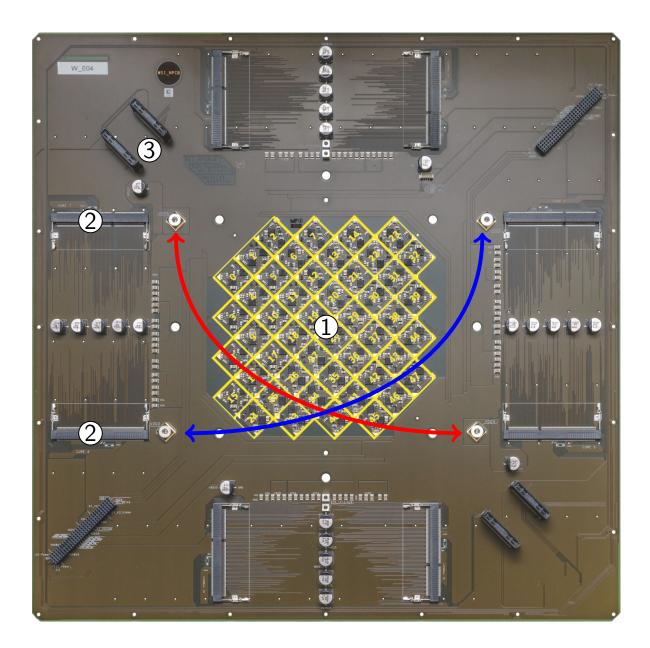


Figure 2.7.: A photograph of the top of the MainPCB (courtesy of Maurice Güttler [1]). The board has a length and width of 43cm. Visible in the center are the PowerFETs (Field Effect Transistors) (1) which switch the power supply of each reticle. These are controlled via the CURE boards (2). In yellow the corresponding Reticle and its position is marked. All 48 Reticles are shown. A single reticle has a width of 20.0482 mm and height of 20.145 mm, with additional space in between reticles of 420 μm horizontally and 250 μm vertically [1]. The top-left and bottom right corner connectors (3) are for the AnaB boards. The main supply voltages V_{DDA} (red) and V_{DDD} (blue) are generated on the PowerIt and inserted at the marked screw connections.

2.2.3. Simple Wafer Resistance Model (SWRM)

When powering any reticle on a wafer system, the voltage setting on the Powerlt side is set to about 1.9 V. This then results in the reticles receiving around 1.8 V. Additionally when running experiments on a HICANN wafer, the current draw results in a drop of this received voltage. This behavior is most likely the result of a resistance between power supply and reticles.

To describe the resistances on such a wafer module, a model can be used. This model combines all resistances introduced through any connection point between supply terminal (copper pad on PowerIt) and PowerFET into R_0 . It also represents the connection between FET and reticle as another resistor R_1 . For this simple model the circuit in figure 2.8 is used.

This naive model will be referenced as SWRM (Simple Wafer Resistance Model) from here.

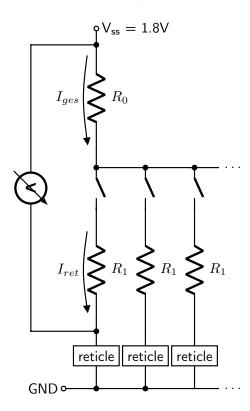


Figure 2.8.: Model of the to measure resistances and their currents, R_0 describes the resistance of a connection between the Powerlt Output and up to the FET (depicted as switch), while R_1 is a Resistance between FET and Reticles. The measurement is done between Output Terminals on the Powerlt and pins on a Analog readout board.

The SWRM circuit consists of two fixed resistance values and their respective currents as approximations of a real world system. It assumes that the connection to the nearest voltage connector is equal (electrically) for all reticles.

In the SWRM, the current flowing through R_1 will be either 0 or a constant current I_{ret} . And the current through R_0 will change depending on the number of reticles that are powered n_{ret}

$$I_{ges} = n_{ret} \cdot I_{ret} \tag{2.17}$$

Therefore the voltage drop V_{drop} as measured by a voltmeter (see figure 2.8) can be described with equation 2.18

$$V_{drop} = V_{R_1} + V_{R_0}$$

= $R_1 \cdot I_{ret} + R_0 \cdot I_{ges}$
= $I_{ret} \cdot (R_1 + R_0 \cdot n_{ret})$ (2.18)

$$V_{\mathsf{drop}} = V_O - V_{\mathsf{off}} \tag{2.19}$$

$$\Rightarrow V_O = I_{\mathsf{ret}} \cdot (R_1 + R_0 \cdot n_{\mathsf{ret}}) + V_{\mathsf{off}}$$
(2.20)

In equations 2.19 and 2.20 reference the desired voltage at reticle level Voff and the voltage at a Powerlt terminal V_O .

3 Experiments

Now that the theoretical model is complete, experiments can be done to start checking that model. The results of these experiments are usable for either voltage or current measurements.

3.1. Experimental Setup

The first setup was used during the calibration phase, while the second setup was used for creating the regulation model.

3.1.1. Calibration Setup

To now calibrate a Powerlt a setup is required that can sweep the input voltage, as well as draw different currents from the Powerlt (see figure 3.1). For that a setup with a bench power supply an electronic load and an external voltmeter are used. Additionally a STM32-Discovery board and a RaspberryPi microcomputer were connected to flash new firmware onto the Powerlt.

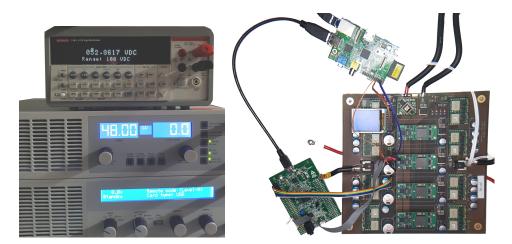


Figure 3.1.: Photographs of the first experimental setup. On the left side visible are a Keithley K2100 voltmeter (top), a Elektro-Automatik PS8080 bench power supply (middle) and EL9080 electronic load (bottom). On the right side visible are a Powerlt with connected STM32-Discovery board (left), and Raspberry PI (top). Also in the picture is the power supply connection (cables at top of Powerlt).

To now calibrate the board the bench supply could be controlled, to sweep through a voltage range, or in a similar fashion the electronic load could sweep through different current draw scenarios.

3.1.2. Power Wafer Setup

To obtain the required measurements for creating a regulation model the second setup was used (figure 3.2). These required measurements are the calculation of I_{ret} , R_0 and R_1 of equation 2.20.



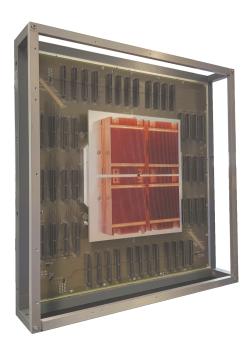


Figure 3.2.: Photographs of the second experimental setup. In this setup the Wafer system assembly was used. This module has a height and length of 50cm and a width of 15cm. The left side shows the back side of the assembly. Here are the Powerlt (1), CURE (3) and AnaB (2) boards mounted, as well as a RaspberryPi (4) and a STM32-Discovery (5). The right side shows the empty front side of the MainPCB and the wafer heat sink.

This setup is similar to a BrainScaleS wafer module as it exists inside the system. But in contrast to these systems there are no FPGAs, AuxPwr or FCP boards (reference [1],fig 2.2). The MainPCB has the PowerWafer attached and is also connected to 8 CURE boards, 2 AnaBs and a PowerIt.

3.2. Characterization

The first experiments to run are the characterization of hardware behavior. These will then result in a Powerlt calibration, which later then can be used as basis for creating a regulation method.

For the complete calibration process the calibration setup was used.

3.2.1. Sampling Time

First up was selecting an optimal sample tick number. The sample ticks are the cycles for which an adc will probe a pin.

In this case the uncalibrated measurement of input voltage was taken as example, and repeated with each of the possible 8 settings.

In addition a voltage measurement was taken with an external voltmeter¹. The voltameter was connected to the 48 V input voltage terminal. The difference from the supplied Voltage, set with the external power supply² was then calculated. In figure 3.3 these calculated values are plotted. The in figure 3.3 contained absolute error of the voltmeter is not 0 but signifficantly different from the power supply voltage. Therefore from here on the reference voltages were taken with the external voltmeter, if possible. This avoids added uncertainty introduced by the power supply.

Also shown are the calculated gain errors, in case of all 8 settings. Important to note is the relative error in only one case not usable. Here the cycleTime-Setting was set to 0 and therefore the smallest available sampling time of 3 Ticks was chosen. This result excludes 0 as a possible value to use. All other measurements are within error margin of each other, and because a smaller time frame is preferred, the best value to use is 1. This results in a sample time of 15 Ticks or 77 ns per pin.

3.2.2. Voltages

Now that a sample time is chosen, it is possible to proceed with the voltage calibration measurements. Note, that measurements can be less accurate, the more components are contained in their respective measurement circuit. The reason for that is, that small errors can accumulate and in e.g. the case of 48V's be amplified by a factor of 8.

48V Input

In this setup the voltmeter is connected to positive and negative input voltage terminal.

When looking at calibrating the input voltage (figure 3.4), we can clearly see a relatively constant offset of $\approx 1V$. This is most likely the result of a offset voltage introduced behind the secondary amplifier. In figure 3.4 a polynomial fit of 2nd degree³ is done and its coefficients extracted (code 1, line 9). These coefficients not only show an offset, but also some deviation in the incline and curve from the default values.

¹Keithley 2100

²

 $^{^{3}\}mbox{A}$ Fit of second degree will be used in the complete calibration process

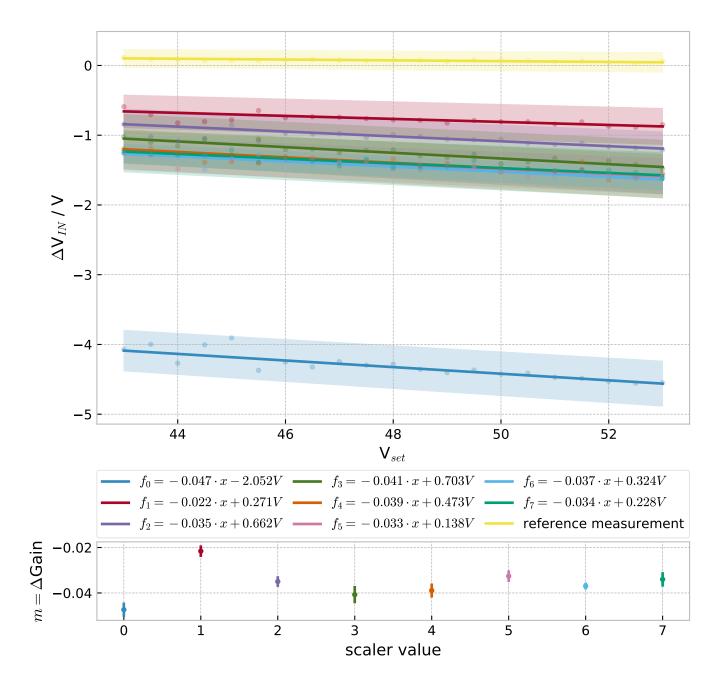


Figure 3.3.: Top: input difference from set voltage vs set voltage for different possible scaler values. Bottom: gain error of the linear fitted curves vs set scaler value (May 29th 2018, \approx 32°C)

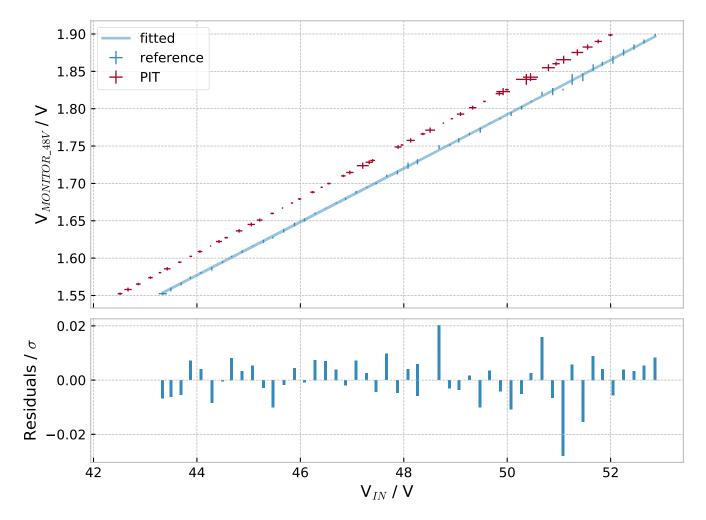


Figure 3.4.: Calibration of 48 V input voltage. Plotted are measured and reference vs the calculated vin voltage. The Calibration sweeps from 43.2 V to 52.8 V. The fit is of second degree and its inverse are the to use calibration coefficients. (fit: $(7.15 \pm 3.59) \times 10^{-5} \text{V}^{-1} V_{\text{IN}}^2 + (2.92 \pm 0.35) \times 10^{-2} V_{\text{IN}} + (1.56 \pm 0.83) \times 10^{-1} \text{V} = V_{\text{MONITOR}_{48V}}$)

9.6V Output

For this setup the voltmeter was connected to a Powerlt GND and 10V pad.

The 9.6V Calibration, shows a slight difference between internal values and the reference measurement. This results in a list of coefficients (code 1, line 7), very similar to those set in the theoretical defaults (??).

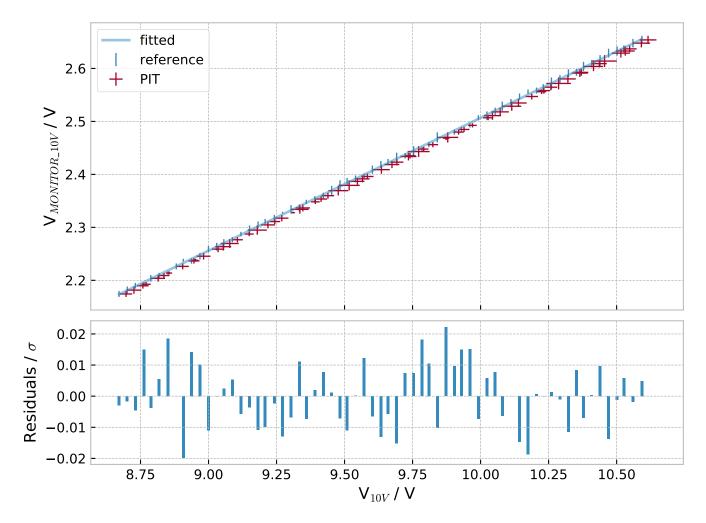


Figure 3.5.: Calibration of 9.6 V input voltage. Plotted are measured and reference vs the calculated vin voltage. The Calibration sweeps from 43.2 V to 52.8 V, and the supply modules divide that into 8.64 V to 10.56 V. The fit is of second degree and its inverse are the to use calibration coefficients. (fit: $(-0.10 \pm 1.23) \times 10^{-3} \text{ V}^{-1} V_{10V}^2 + (2.53 \pm 0.24) \times 10^{-1} V_{10V} + = V_{\text{MONITOR}_10V}$)

This small difference is explained by the simple voltage division used as our circuitry, and no amplification, as for the input voltage circuit.

1.8V Output

The last voltage to calibrate is divided into two domains, one for supplying the analog, and one for the digital side of the wafer circuitry. Each deliver between 1.549 V and 2.022 V and both are settable by their respective circuit (both as in figure 2.4).

And for each measurement the voltmeter was either connected to POwerlt GND and 1.8V analog or 1.8V digital pins.

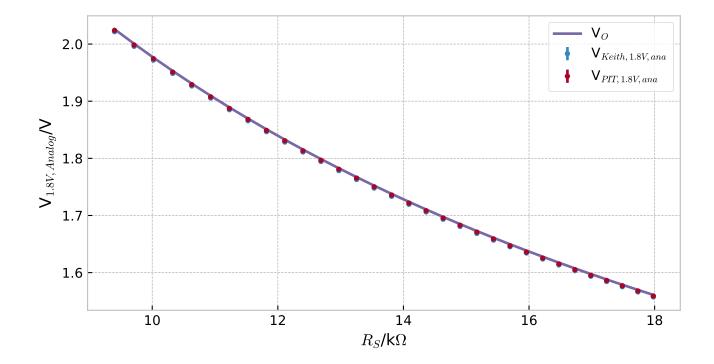


Figure 3.6.: Calibration: analog 1.8V Output voltage, plotted are external measurement and internal values vs set resistance R_S at the voltage module.

Visualized in figure 3.6 is the analog domains calibration, showing nearly no difference in board and reference measurements. Mostly due to direct connection between created voltage and the STM-Chips pin.

3.2.3. Currents

With now calibrated Voltages, the next step is to measure the behavior of the current measuring circuits. Note that the 9.6V Output does in fact not have a include circuit for measuring its current draw, and that this number will be obtainable from all other (calibrated) measurements.

48V Input

This experiment will calibrate the 48V input current. The setup consists of connecting the electric load to GND and 10V pins. In it the current drawn by the Powerlt sweeps over a range from 0 A to 20 A.

In figure 3.7 quite a gap between observed and measured values can be seen. This is most likely a gain error, which would result in a error in m_2 , as observed. And the fitted curve has the following parameters:

$$V_{\text{MONITOR}_48I} = m_0 + m_1 \cdot I_{\text{IN}} + m_2 \cdot I_{\text{IN}}^2$$

$$m_0 = (2.64 \pm 1.01) \times 10^{-3} \text{ V}$$

$$m_1 = (5.63 \pm 0.25) \times 10^{-3} \text{ V A}^{-1}$$

$$m_2 = (1.36 \pm 0.13) \times 10^{-4} \text{ V A}^{-2}$$
(3.1)

from which the inverse will used for calibration inside the Powerlt.

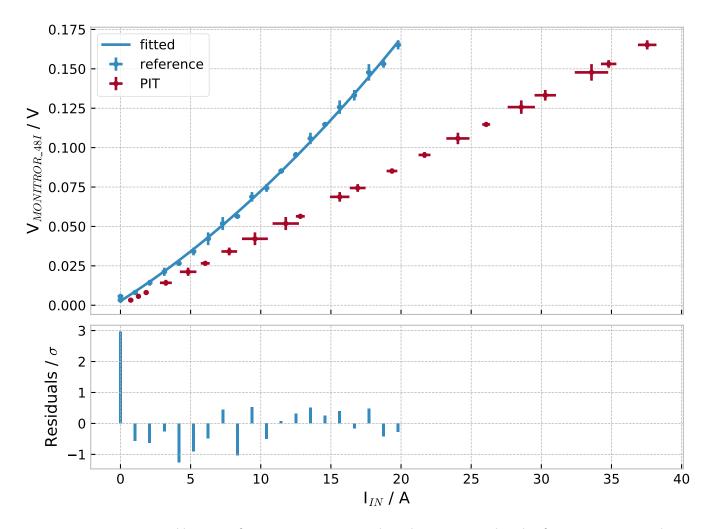


Figure 3.7.: Calibration of 48 V input current. Plotted are measured and reference current vs the calculated pin voltage. The Calibration sweeps over 0 A to 20 A. The fit is of second degree and its inverse are the to use calibration coefficients.

1.8V Output

For the calibration experiment of both 1.8V output currents, the current draw ranged from 0 A to 90 A. The electric load was connected to a GND and 1.8V analog or 1.8V digitalpin

depending on the measurement. Observed were the values in figure 3.8. Visible is a different incline of internal measurement and reference.

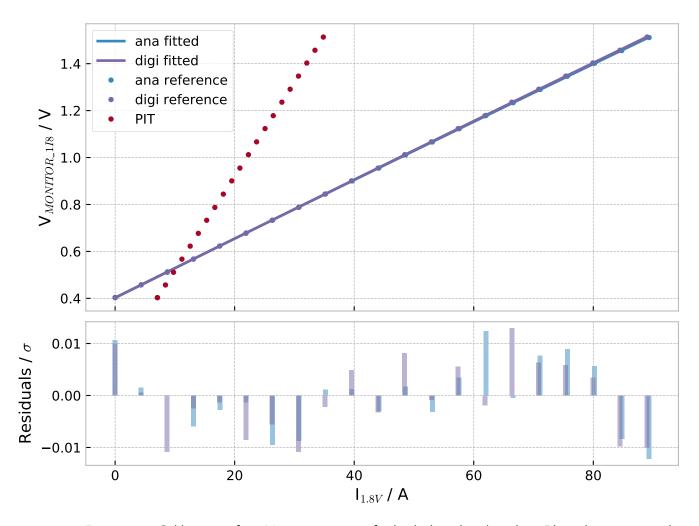


Figure 3.8.: Calibration of 1.8 V output current for both digital and analog. Plotted are measured and reference current vs the calculated pin voltage. The Calibration sweeps over 0 A to 90 A. The fits are of second degree and their inverse are the to use calibration coefficients.

The fitted curve for the analog side were:

$$V_{\text{MONITOR_118_ANA}} = m_0 + m_1 \cdot I_{1.8V, \text{ ana}} + m_2 \cdot I_{1.8V, \text{ ana}}^2$$
(3.2)
$$m_0 = (4.03 \pm 0.00) \times 10^{-1} \text{ V}$$
$$m_1 = (1.26 \pm 0.00) \times 10^{-2}$$
$$m_2 = (-2.33 \pm 0.27) \times 10^{-6} \text{ V}^{-1}$$

, while the digital side had quite similar values of:

$$V_{\text{MONITOR}_118_\text{DIGI}} = m_0 + m_1 \cdot I_{1.8\text{V, digi}} + m_2 \cdot I_{1.8\text{V, digi}}^2$$
(3.3)
$$m_0 = (4.02 \pm 0.01) \times 10^{-1} \text{V}$$

$$m_1 = (1.27 \pm 0.00) \times 10^{-2}$$

$$m_2 = (-1.90 \pm 0.31) \times 10^{-6} \text{V}^{-1}$$

This also show, that both parts are so similar in behavior, that a single sides observations would have sufficed.

3.3. 1.8V Regulation

As Described beforehand the Output Voltages for both analog and digital can be adjusted to some degree and therefore we can compensate for the dropoff occurring between Powerlt Output Terminals and Reticles.

The following experiments were run unsing the Power Wafer setup. To run any test with the PowerWafer, the patterns in figure 3.9 were used. There are two reasons for that, firstly these patterns distribute the current draw in a regular fashion as to distribute the load between the connectors. Secondly, when powering Reticles all of the energy is converted into heat, via the ohmic resistors.

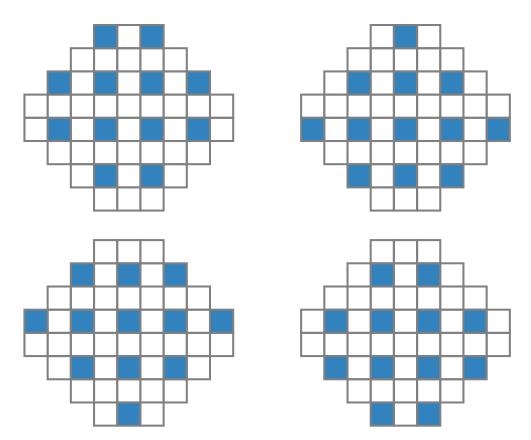


Figure 3.9.: Used regular patterns for current tests on PowerWafer

And although the copper heat sink and fans (see figure 3.2), should be able to handle this heat in a HICAN wafer system, when grouping together reticles and powering them, the dissipation does not suffice. This is the case, because the Power Wafer is drawing more current per reticle than a HICANN wafer would during an experiment. The internal temperature probes (between heat sink and wafer) register well above $50 \,^{\circ}$ C, when grouping 3 or more reticles.

3.3.1. Characterization of Dropoff

Wanting to observe and characterize the voltage drop, first the connections between Powerlt and Reticles can be measured with the in figure 2.8 described connections, which in actuality are the PowerlT Terminal and corresponding analog readout pin on a Analog readout board.

To use the PowerWafer for testing one of the patterns in figure 3.9 will be used, each pattern has a approximate current draw of 120A and will distribute heat and draw per terminal evenly.

In figure 3.10 a single reticles (#40) voltage drop for different Current Draws is visualized. A relatively linear trend and residuals of a trigonometric behavior can be observed (most likely the result of the inaccurately measurable current draw, which here is done inside the Powerlt).

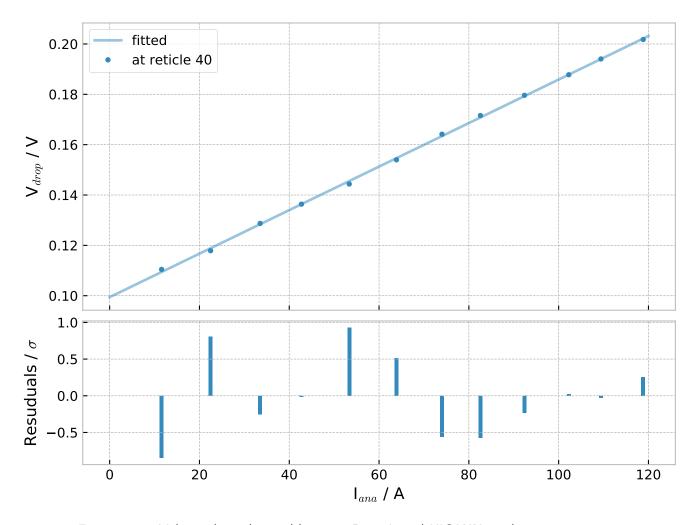


Figure 3.10.: Voltage drop observed between Powerlt and HICANN, each point represents a state after enabling additional Reticles on the PowerWafer (right upper wafer in figure 3.9)

Here a Voltage Drop vs. Current draw of the wafer shows a linear behavior and therefore can be regulated on basis of the current measurement done by on board Measurement circuit.

3.3.2. Numerical-Correction (Regulation)

The initial idea, to approach the correction of this dropoff is a Numerical: the SWRM (subsection 2.2.3) and its corresponding Equations can be applied here. equation 2.16, which maps the measured output current to a corresponding potentiometer setting, requires the Dropoff to be linear, which was observed.

To apply this approach, two assumptions need to be made:

- all reticles have the same current draw (already not accurate, see figure 3.10)
- all reticles experience the same voltage drop (as observed for reticle 40)

and the following four values are required, before a regulation can be attempted:

- *I_{ret}*, the current draw of a single reticle,
- R_0 , the resistance between Powerlt and FET,
- R₁, the resistance of a single Reticle
- Voff, the wanted Voltage at a Reticle

To get a representative value of I_{ret} for use in the SWRM, the mean current draw per reticle was taken (figure 3.11):

$$I_{\rm ret,mean,corr} = (9.9 \pm 0.6) \, \mathsf{A} \tag{3.4}$$

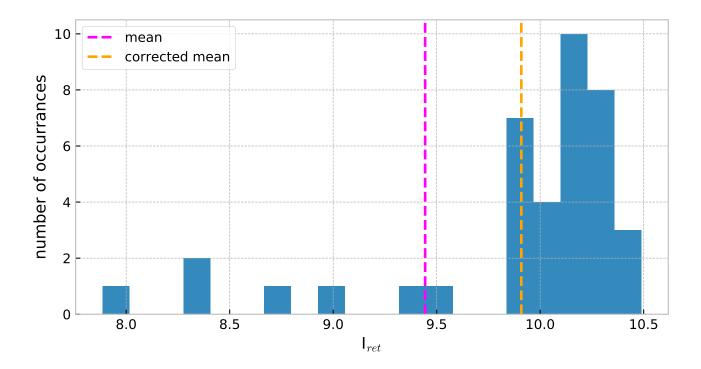


Figure 3.11.: Distribution of analog current draw for all reticles on the PowerWafer (which were possible to measure)

The figure 3.11 was obtained by measuring the increase in current draw for each reticle, for each of the 4 patterns (figure 3.9).

To obtain R_0 , the pattern in figure 3.12 was used to take measurements for both the neighborhood as well as the farthest reticles.

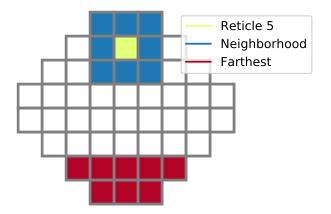


Figure 3.12.: Reticles used to determine correlation between distance and Voltage Drop

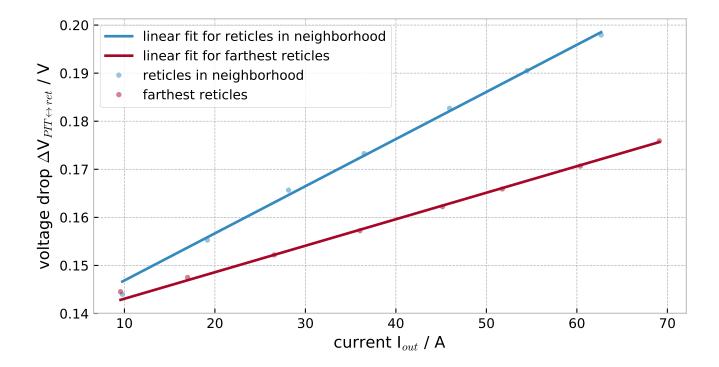


Figure 3.13.: Voltage drop vs current for both Reticles in direct neighborhood and farthest possible Reticles

From figure 3.13 it is possible to see that the distance between reticles that are used gives different behavior of the voltage drop. Both Inclines happen to be the extreme cases, while either being completely uncorrelated, the case for farthest Reticles, or being directly correlated by their distance, here observable for the neighboring Reticles.

Therefore we obtain two values for R_0 :

$$R_{0,\text{neighbor}} = (7.1278 \pm 0.1567) \,\mathrm{m}\Omega$$

$$R_{0 \text{ farthest}} = (4.0079 \pm 0.0537) \,\mathrm{m}\Omega$$
(3.5)

from the same measurement it is also possible to extract R_1 by extrapolating to 0, which results in:

$$\begin{aligned} R_{1,\text{neighbor}} &= (14.1708 \pm 0.1779) \,\mathrm{m}\Omega \\ R_{1,\text{farthest}} &= (14.2218 \pm 0.1503) \,\mathrm{m}\Omega \end{aligned} \tag{3.6}$$

here the values obtained are within error margin of each other. So applying these Values, the following behavior for regulation can be visualized:

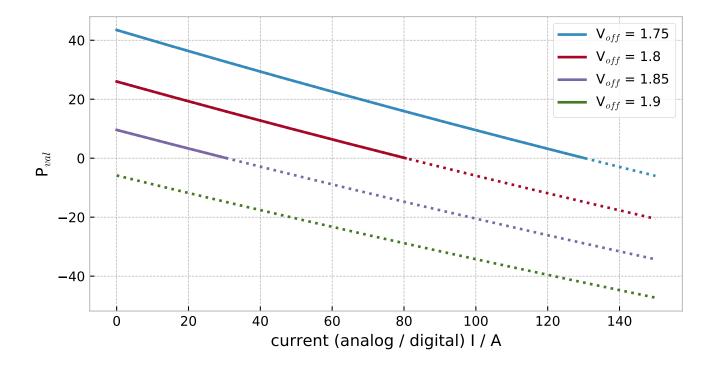


Figure 3.14.: Possible P_{val} curves after SWRM, dotted lines represent not achievable values. This plot is generated from the obtained SWRM parameters, leaving only V_{off} to vary.

The in figure 3.14 visualized values show the theoretical P_{val} for the corresponding current. All of the dotted parts depict with this setup unachieveble values. This results in the Powerlts inability to correct for any change in current above a certain threshold. In the domain above this threshold the resulting voltage would behave the same as before regulation. Note that the 1.8V regulation, should fail at about 80A of current draw.

Now voltage drop per reticle, in a single reticle power state, was observed:

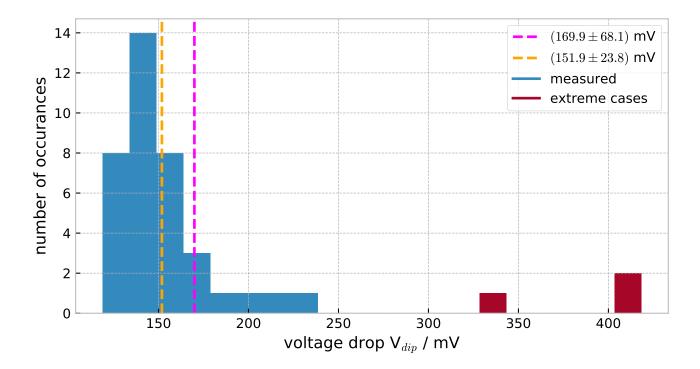


Figure 3.15.: Initially observed voltage drop, red values are ignored for corrected mean

The histogram in figure 3.15 has amean of

$$V_{\rm dip,mean,corrected} = (151.8811 \pm 23.8138) \,\mathrm{mV}$$
 (3.7)

figure 3.16 shows how those Voltages are Distributed over the complete PowerWafer. All white Reticles are not measurable, either because they were not functional or could not be read. The occurances marked in red in figure 3.15 are reticles #11, #20 and #28, which were outliers and are excluded in the calculation of corrected values.

This results in a distribution, which when combined with the spread of R_0 from figure 3.13, gives an approximate range for all reticles voltage drop at a given current draw (??).

To be able to obtain the through AnaB pins measured voltages it should also be possible to use the CUREs voltage readout. The voltages obtained from these boards, should be comparable. The reason for that is that we can assume a constand R_1 for all reticles. In figure 3.17 these voltages are visualized, in comparison to the AnaB voltages.

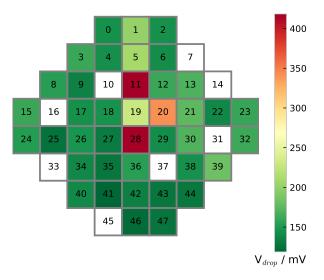


Figure 3.16.: V_{drop} distribution over full Power Wafer; White have no measurement; Red an Orange are marked red in figure 3.15

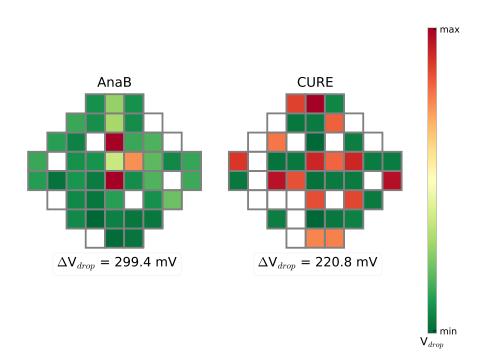


Figure 3.17.: Comparison of AnaB and CURE measured voltage drop. Colors indicate their respective relative values for each measurement. White reticles have no measurement.

This comparison shows no discernable relation between both measurements. The reason for this is most likely a problem in the assumption, that R_1 is the same for all reticles, which would result in a voltage difference that is constant. Additionally the distribution of CURE voltages would look similar to the AnaB measurement.

4 Results

In this chapter all results from the experiments, as well as reasons will be discussed.

4.1. Calibration

This calibration process yielded some workflows for use inside the system as well as calibration values for the used Powerlt.

4.1.1. Calibration-Database

The obtained calibration values for the in these experiments used Powerlt, are combined in code 1.

```
id: '0x280029000F51333332343638'
name: B05
poly18iana: [-31.5155, 78.516, -0.0688]
poly18idigi: [-31.3536, 78.3701, -0.196]
poly18i: [-31.4396, 78.443, -0.1324]
poly48i: [-0.1765, 153.0021, -204.1858]
poly10v: [0.6348, 3.459, 0.1118]
poly48v: [-4.5248, 33.3195, -1.6167]
poly18v: [0.0234, 0.9728, 0.0072]
```

Code 1: PITDB entry for B05 Powerlt. id is obtained by the firmware and unique to each STM32Chip. The name corresponds to the label on each Powerlt. All poly* are all polynomial coefficients in order of 0th degree to 2nd degree.

And to compare, the values in code 2 are theoretical values, obtained from all equations in chapter 2.

```
uuid: 'default'
name: 'Bxx'
poly18i: [-3.0, 25.0, 0.0]
poly48i: [0.0, 227.27, 0.0]
poly10v: [0.0, 4.0, 0.0]
poly10v: [0.0, 1.0, 0.0]
poly18v: [0.0, 27.386, 0.0]
```

```
Code 2: Default PITDB entry for any Powerlt. All poly* are all polynomial coefficients in order of 0th degree to 2nd degree.
```

4.1.2. Accuracy

To obtain an accuracy for the internal measurements, the experimental sweeps can be repeated after calibration. One example of a calibrated measurement can be seen in figure 4.2.

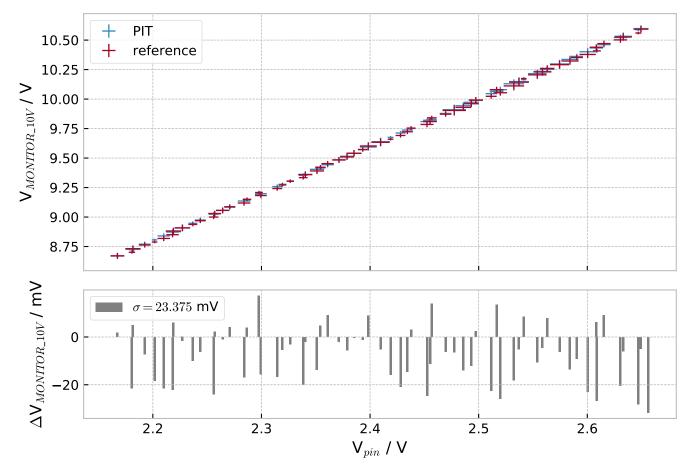


Figure 4.2.: Voltages after calibration. Sweep from 43.2 V to 52.8 V input voltage resulting in a range from 8.64 V to 10.56 V. The errors in the bottom diagram show the differences between reference and PIT values.

This repeats the calibration measurement for 9.6 V. Here quite similar values can be observed, with a maximum ΔV of around 31.7 mV. It is also possible to see a systematic error in figure 4.2. This error could be corrected, but requires further iterations of the calibration procedure. Additional iterations would allow for a reduction of ΔV , up to a value of 24.5 mV ($\approx 0.25\%$).

In comparison to this, the 1.8 V measurement should have a bit better accuracy because of the even simpler circuit.

$$0.25\,\%\cdot 1.8\,Vpprox 4.5\,mV$$

And also the accuracy of measuring 48 V should be worse than 24 mV, again because of the circuits complexity.

$$0.25\,\%\cdot48\,Vpprox120\,mV$$

4.2. Regulation

THese are the obtained results from attempting to regulate the 1.8 V terminals.

4.2.1. Without Regulation

Before the regulation could be attempted some parameters were needed to complete the SWRM, see equations 3.4, 3.5 and 3.6. With these values and their respective (error) ranges the in figure 4.3 found plot could be created.

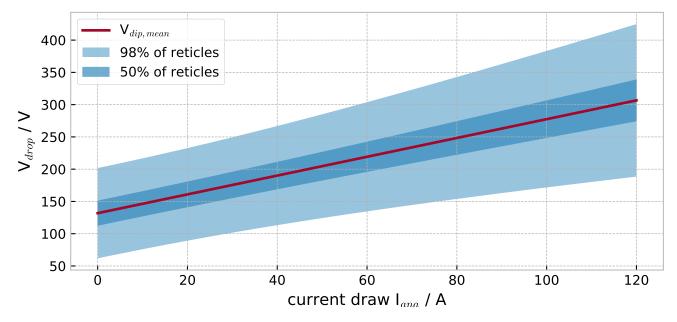


Figure 4.3.: Plot of the expected range of V_{drop} for different current draw. This result is the expected spread without any regulation. Shown are the range for 98% and 50% of reticles, as well as the mean V_{drop} for all reticles.

In figure 4.3 the expected spread of V_{drop} can be found. This spread is the worst case scenario of V_{drop} distribution. The reason for that is that with a regulated voltage a constant Vdrop is expected. This applies to all currents up until $\approx 80\,A$, becase from there the regulation would not work anymore and V_{drop} would behave like in the unregulated case.

4.2.2. With Regulation

To verify the regulation is working and to see if the prediction in figure 3.14 is correct new values were measured. These Values are the voltages with regulation enabled at different Reticles (see figure 4.4).

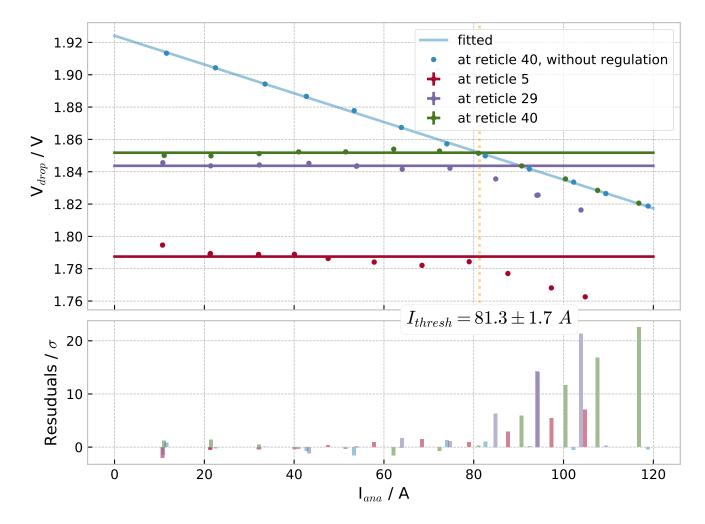


Figure 4.4.: Observed AnaB voltages after regulation at multiple reticles. Reticle #40 shows the best-case scenario with the least amount of V_{drop} . Reticle #5 is a worst-case scenario, with the highest V_{drop} while still being a usable reticle.

In figure 4.4 three different reticles (#5, #29 and #40) were measured. Observable is, that firstly the regulation, which was set to achieve 1.8 V is working until I_{ana} is at $I_{thresh} = 80$ A. There the minmal potentiometer setting is used. From here V_{drop} behaves the same as without regulation.

Secondly the voltages for different reticles is different and not equal. This was one of the assumptions in the SWRM. To describe that behavior a distance based model (subsection 4.2.3: DWRM) could be the solution.

And third, under the assumption of a constant fit (up to $I_{ana} \approx 80 \text{ A}$) a systematic error can be observed.

Also, the expected behavior from section 4.2 can be observed.

Additionally if the range of $I_{ana} > I_{thresh}$ is observed, V_{drop} does not increase by more than about 30 mV.

4.2.3. Distance Wafer Resistance Model (DWRM)

So far, the discussed measurements and SWRM have been enough to create a first iteration regulation mechanism. Until now assumptions like a constant R_0 over the complete Wafer, have driven the creation of equations to satisfy this model. They also led to observable inaccuracies, as seen in equation 3.5. Although the SWRM approximates the real world, it is not exact enough. To further develop a model that could describe the real world setup in a better way, the next model would have to describe e.g. a different R_0 .

In a wafer, the distance between reticles and voltage connector (see figure 2.7) are resulting in additional resistance.

Therefore the DWRM could be adapted. Circuit 4.5 visualizes a model, in which each different distance from the voltage connector, is classified with an additional resistance.

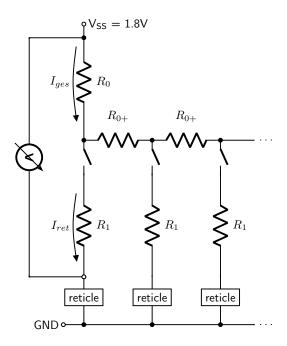


Figure 4.5.: Modified model of the to measure resistances and their currents. Similar to SWRM R_0 describes the resistance of a connection between the Powerlt Output, up to the FET (depicted as switch), while R_1 is a Resistance between FET and Reticles. But additionally R_{0+} described a Resistance, that depends on the distance between reticle and voltage connector. The measurement is done between output terminals on the Powerlt and pins on a Analog readout board

With this model the voltage is now expected to change depending on the reticles distance instead of being the same. The distances inside a wafer are visualized in figure 4.6

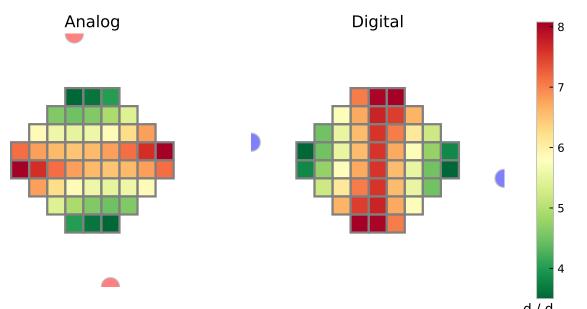


Figure 4.6.: Distances of reticles to the nearest voltage supplying connection for DWRM, distance is in reticle-side length

5 Outlook

All in all the set goals were achieved.

While all of the measurements could be calibrated they can still be fine tuned. As shown in figure 4.2, the error of a calibrated measurement is not quite minimal. In the future it would be possible to make these even more accurate, either by using a different method for calculating, which is not based on second degree polynomials. Or by further calibration, as mentioned in the results chapter.

The voltage distribution, as described in figures 3.15 and 3.16, was quantified and the SWRM could be used for creating a worst-case V_{drop} distribution as seen in figure 4.3. Therefore a first iteration of a usable regulation mechanism could be implemented and verified (see figure 4.4). This mechanism allows for a certain degree of regulation until a current threshold is reached. This threshold was also agreeing with a beforehand calculated value of around 80 A

For further developing this the more complex DWRM could be used. This would allow for a more accurate regulation, that would narrow down the worst-case scenario of figure 4.3. For that model to work, each experiment run on a wafer, in the system, would require a simulation of the distribution of voltage between the used reticles. As to minimize the maximum difference in voltage drop. This could also factor in the number of active HICANNs per reticle.

Additionally the current threshold is restricted by the internally used resistor chain (described in figure 2.4). If the minimum resistance of that circuit were to be changed, the threshold would move up in current.

I Appendix - Firmware

I.1. Virtual Memory Mapping

THe biggest Change done to the Firmware was the implementation of a new communication protocol. This protocol uses the following table as reference

I.2. How to calibrate a Powerlt Board

The Calibration process is based on the PItSTOP Python scripts¹. These are split into <code>server</code> and <code>aggregator</code>. While the Server is handling the translation between raw l²C data, and the JSON formatted result, the Aggregator takes this JSON and calculates a calibration.

Using the script any one of the following Values can be tested and calibrated:

- Input Voltage (pitstop.Aggregator.test_v_48())
- Input Current (pitstop.Aggregator.test_i_48())
- 9.6V Output Voltage (pitstop.Aggregator.test_v_10())
- 1.8V Output Voltage (pitstop.Aggregator.test_v_18())
- 1.8V Output Current (pitstop.Aggregator.test_i_18())

I.2.1. Setting up the Test Environment

The simplest way to setup an environment consists of cloning the PItSTOP project on a client:

```
> git clone https://url.to.pitstop
```

then substituting the rsync target:

```
all:
rsync --progress ./*.py /remote.url/
```

, to be your server (should be a RaspberryPi connected to the Powerlt)

¹ PItSTOP repository

addr	name	type	size	perm
0x00	onmask	byte	1	rw
0x01	offmask	byte	1	rw
0x02	anapot	9bit	2	rw
0x04	digipot	9bit	2	rw
0x06	polyFit.V48	float arr	12	rw
0x12	polyFit.I48	float arr	12	rw
0x1e	polyFit.V8	float arr	12	rw
0x2a	polyFit.V18	float arr	12	rw
0x36	polyFit.I18	float arr	12	rw
0x42	polyFit.T	float arr	12	rw
0x4e	sampleTicks	byte	1	rw
0x4f	V_out	float	4	rw
0x53	TEMP_SENSOR	float	4	r
0x57	EXT_AIN	float	4	r
0x5b	MONITOR_48V	float	4	r
0x5f	MONITOR_48I	float	4	r
0x63	MONITOR_8VBUS	float	4	r
0x67	MONITOR_8IBUS	float	4	r
0x6b	MONITOR_8V_0	float	4	r
0x6f	MONITOR_8V_1	float	4	r
0x73	MONITOR_8V_2	float	4	r
0x77	MONITOR_8V_3	float	4	r
0x7b	VDD_1V8_ANA	float	4	r
0x7f	VDD_1V8_IOUT_ANA	float	4	r
0x83	VDD_1V8_DIGI	float	4	r
0x87	VDD_1V8_IOUT_DIGI	float	4	r
0x8b	CommitHash	float	4	S
0x8f	CommitDirtyFlag	byte	1	S
0×90	STM32UUID	96bit	12	S

Figure I.1.: memory mapping of the packed struct moved over i2c, addr is the address to use, type is the c++ type, size is in bytes and perm denotes read-writability. writability

Figure I.2.:

I.2.2. Running a Test

Running the test requires the following commands Serverside:

```
> python server.py
```

Clientside:

> python aggregator.py

Now just following the instructions given, the selected test can be run:

The result will consist of two diagrams one without calibration and one with. It will also write the newly obtained calibration data into pitdb.yaml

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Ich versichere, dass ich diese Arbeit selbstständig verfasst und keine anderen als die angegebenen Quellen und Hilfsmittel benutzt habe.

Heidelberg, 29. August 2018,

(signature)